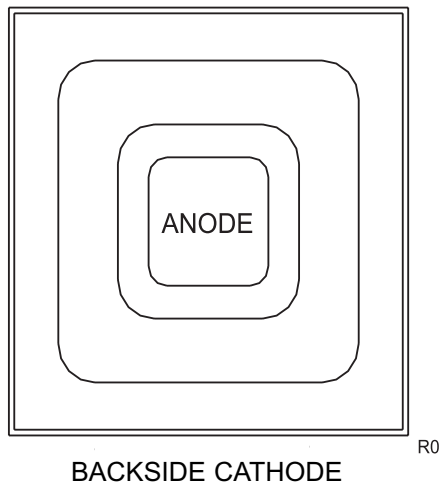


**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	11 x11 MILS
Die Thickness	7.1MILS
Anode Bonding Pad Area	3.3 x 3.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

**Geometry**



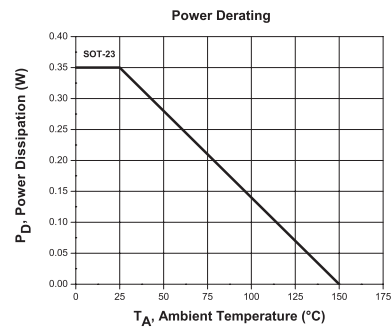
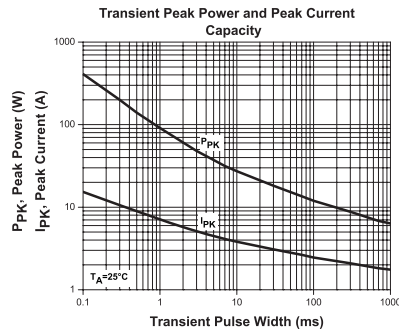
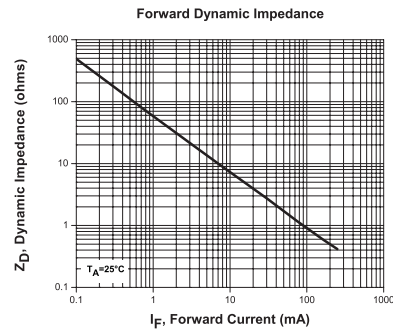
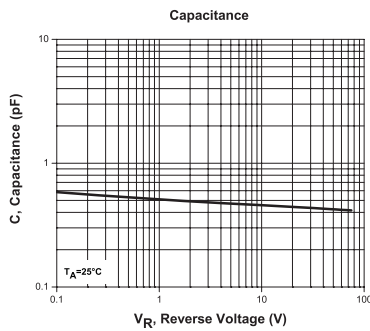
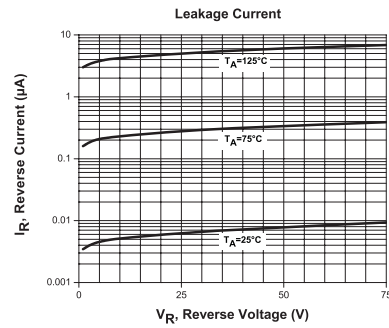
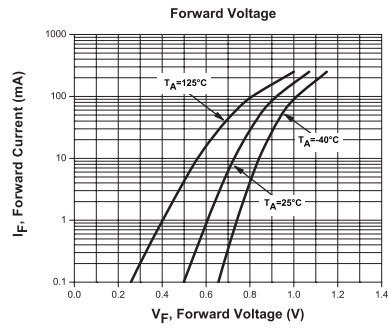
**GROSS DIE PER 4 INCH WAFER**  
89,376

**PRINCIPAL DEVICE TYPES**

CMPD914  
CMPD4448  
1N914  
1N914B  
1N4148  
1N4448  
1N4154  
1N4454  
CMPD2836  
CMPD2838  
CMPD7000

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